Record Nr. UNINA9910146964203321 Autore Rohde Ulrich L Titolo RF/microwave circuit design for wireless applications / / Ulrich L. Rohde, David P. Newkirk New York, : John Wiley, c2000 Pubbl/distr/stampa **ISBN** 1-280-26471-3 9786610264711 0-470-35013-X 0-471-46380-9 1-60119-405-6 0-471-22413-8 Descrizione fisica 1 online resource (977 p.) Altri autori (Persone) NewkirkDavid P Disciplina 621.381/32 621.3815 Soggetti Microwave integrated circuits - Computer-aided design Wireless communication systems - Equipment and supplies - Design Semiconductors - Computer-aided design Radio frequency Lingua di pubblicazione Inglese **Formato** Materiale a stampa Livello bibliografico Monografia "A Wiley-Interscience publication." Note generali Nota di bibliografia Includes bibliographical references and index. Contents: Foreword: Preface: 1 Introduction to Wireless Circuit Design: Nota di contenuto 1-1 Overview; 1-2 System Functions; 1-3 The Radio Channel and Modulation Requirements; 1-3-1 Introduction; 1-3-2 Channel Impulse Response; 1-3-3 Doppler Effect; 1-3-4 Transfer Function; 1-3-5 Time Response of Channel Impulse Response and Transfer Function; 1-3-6 Lessons Learned; 1-3-7 Wireless Signal Example: The TDMA System in GSM; 1-4 About Bits, Symbols, and Waveforms; 1-4-1 Introduction; 1-4-2 Some Fundamentals of Digital Modulation Techniques; 1-5 Analysis of Wireless Systems 1-5-1 Analog and Digital Receiver Designs1-5-2 Transmitters; 1-6 Building Blocks; 1-7 System Specifications and Their Relationship to Circuit Design; 1-7-1 System Noise and Noise Floor; 1-7-2 System

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Sommario/riassunto

A unique, state-of-the-art guide to wireless integrated circuit design. With wireless technology rapidly exploding, there is a growing need for circuit design information specific to wireless applications. Presenting a single-source guidebook to this dynamic area, industry expert Ulrich Rohde and writer David Newkirk provide researchers and engineers with a complete set of modeling, design, and implementation tools for tackling even the newest IC technologies. They emphasize practical design solutions for high-performance devices and circuitry, incorporating ample examples of novel and